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### Amendments to the Specification

Please amend the Title of the Invention as follows:

**METHODS FOR FABRICATING A TRIPLE-GATE MOSFET TRANSISTOR AND**  
**METHODS FOR FABRICATING THE SAME**

*Dhu  
3/10/05*

Please amend the paragraph beginning of page 1, line 5 as follows:

This application is related to U.S. Patent Application Serial No. \_\_\_\_\_  
(Attorney Docket No. TI-36030) 10/696,130, filed on 10/29/2003  
\_\_\_\_\_, entitled MULTIPLE GATE MOSFET DEVICE WITH  
LITHOGRAPHY INDEPENDENT SILICON BODY THICKNESS AND METHODS  
FOR FABRICATING THE SAME.